

ELIMINATION OF DENDRITE FORMATION DURING METAL/ CHALCOGENIDE GLASS DEPOSITION

Abstract of the Disclosure

A method of forming a programmable conductor memory cell array is disclosed wherein metal and chalcogenide glass are co-sputtered to fill an array of cell vias in a prepared substrate. The prepared substrate is heated above room temperature before the metal and chalcogenide glass film is deposited, and the heating is maintained throughout the deposition. The resulting metal/chalcogenide glass film has good homogeneity, a desired ratio of components, and has a regular surface.

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